

Title (en)  
LINE-INTEGRATED SEMICONDUCTOR SWITCH AND METHOD FOR PRODUCING SAME

Title (de)  
LEITUNGSINTEGRIERTER HALBLEITERSCHALTER UND VERFAHREN ZU DESSEN HERSTELLUNG

Title (fr)  
COMMUTATEUR SEMI-CONDUCTEUR À CONDUCTEURS INTÉGRÉS ET SON PROCÉDÉ DE FABRICATION

Publication  
**EP 3469664 A1 20190417 (DE)**

Application  
**EP 17714166 A 20170322**

Priority  
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• EP 2017056761 W 20170322

Abstract (en)  
[origin: WO2017215798A1] Line-integrated switch comprising at least one first metallic flat part 2, at least one second metallic flat part 8, wherein the flat parts are arranged with the broad sides thereof one above another in an overlap region and, in the overlap region, a semiconductor switch 18 is arranged between the flat parts 2, 8, in a manner connecting the flat parts 2, 8 to one another in a switching fashion. A simple construction is possible by virtue of the fact that, at least in the overlap region, a first one of the flat parts 2 is at least partly coated with an insulation on a side facing the second one of the flat parts 8, wherein a cutout is provided in the insulation in a contact region 10 and the semiconductor switch 18 is electrically contacted with the flat part 8 in the contact region 10.

IPC 8 full level  
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CPC (source: EP US)  
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Citation (search report)  
See references of WO 2017215798A1

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